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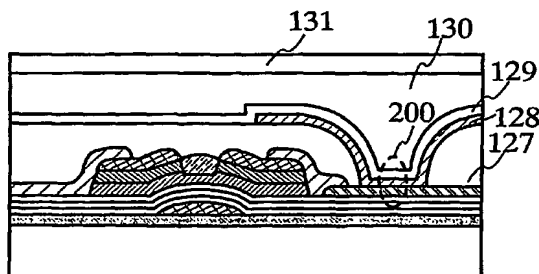
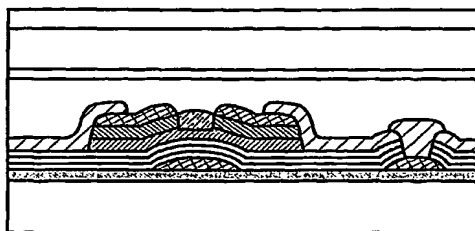
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(54) Title: LIGHT-EMITTING DEVICE AND METHOD FOR MANUFACTURING THE SAME



(57) Abstract: Especially in case that a light-emitting element composed of layers containing organic compounds or inorganic compounds is driven by a thin film transistor (TFT), a structure having at least two transistors installed with a drive TFT is required to prevent irregularities of ON current of a switching TFT provided to a pixel region. Hence, the simplification of a semiconductor element structure and a process for manufacturing a semiconductor element becomes an urgent task as a large substrate is frequently used. According to the present invention, after that a source region and a drain region are formed, an insulating film serving as a channel protective film is formed to cover a portion for serving as a channel region, then, an island-like semiconductor film is formed. Accordingly, a semiconductor element can be manufactured by using only a metallic mask without forming a resist mask, and so the process can be simplified.

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